In the Claims:

Please amend claims 1 and 5 to read as follows. A marked up copy of the claims, showing the changes, is attached.

1. (Amended) A film-forming method for forming a deposited film on a substrate arranged in a substantially enclosed film-forming vessel by means of plasma CVD, said film-forming vessel being provided with a raw material gas introduction means and an exhaustion means, said film-forming method comprising the steps of introducing a raw material gas comprising at least a hydrogen gas and a silicon-containing raw material gas into said film-forming vessel through said raw material gas introduction means, maintaining an inner pressure of said film-forming at a desired value by means of said exhaustion means and introducing a high frequency power into said film-forming vessel through a discharge electrode provided in said film-forming vessel to generate a plasma in a plasma generation region between said substrate and said discharge electrode in said film-forming vessel thereby forming said deposited film on said substrate maintained at a desired temperature, characterized in that the formation of said deposited film on said substrate is performed while applying a periodicity voltage having at least two different waveform components having a different amplitude to an auxiliary electrode arranged at a position in said plasma generation region of said film-forming vessel.

5. (Amended) A film-forming method for forming a deposited film on a substrate arranged in a substantially enclosed film-forming vessel by means of plasma CVD, said film-forming vessel being provided with a raw material gas introduction means and an exhaustion means, said film-forming method comprising the steps of introducing a raw material gas comprising at least a hydrogen gas and a silicon-containing raw material gas into said film-forming vessel through said raw material gas introduction means, maintaining an inner pressure of said film-forming at a desired value by means of said exhaustion means and introducing a high frequency power into said film-forming vessel through a discharge electrode provided in said film-forming vessel to generate a plasma in a plasma generation region between said substrate and said discharge electrode in said film-forming vessel thereby forming said deposited film on said substrate maintained at a desired temperature, characterized in that said substrate is retained in a state of having a floating potential is said film-forming vessel, an auxiliary electrode is provided on a side opposite a film-forming face of said substrate in said film-forming vessel, such that said auxiliary electrode is electrically isolated from said substrate, and the formation of said deposited film on said substrate is performed while applying a periodicity voltage having at

least two different waveform components having a different amplitude to said auxiliary electrode.

Add the following new claim:

9. (New) A film-forming method for forming a deposited film on a substrate arranged in a substantially enclosed film-forming vessel by means of plasma CVD, said film-forming vessel being provided with a raw material gas introduction means and an exhaustion means, said film-forming method comprising the steps of introducing a raw material gas comprising at least a hydrogen gas and a silicon-containing raw material gas into said film-forming vessel through said raw material gas introduction means, maintaining an inner pressure of said film-forming at a desired value by means of said exhaustion means and introducing a high frequency power into said film-forming vessel through a discharge electrode provided in said film-forming vessel to generate a plasma in a plasma generation region between said substrate and said discharge electrode in said film-forming vessel thereby forming said deposited film on said substrate maintained at a desired temperature, characterized in that the formation of said deposited film on said substrate is performed while applying a periodicity voltage having at least two different waveform components having a different amplitude to an auxiliary electrode arranged either at a position in said plasma generation region of said film-forming vessel or on a side opposite a film-forming face of said substrate in said film-forming vessel.

REMARKS

Claims 1 to 8, as amended, and new claim 9 appear in this application for the Examiner's review and consideration. Claims 1, 5, and 9 are independent. The amendments to claims 1 and 5 corrects a minor informality unrelated to patentability. The amendments and the new claim are fully supported by the specification and the original claims, as filed. Therefore, there is no issue of new matter.

The Examiner required election required under 35 U.S.C. § 121 to a single disclosed species for prosecution on the merits to which the claims shall be restricted if no generic claim is finally held to be allowable for the reasons set forth on pages 2 and 3 of the Office Action.

In response, Applicants provisionally elect with traverse Group I, claims 1 to 4, drawn to a plasma deposition method without isolation between the substrate and the